

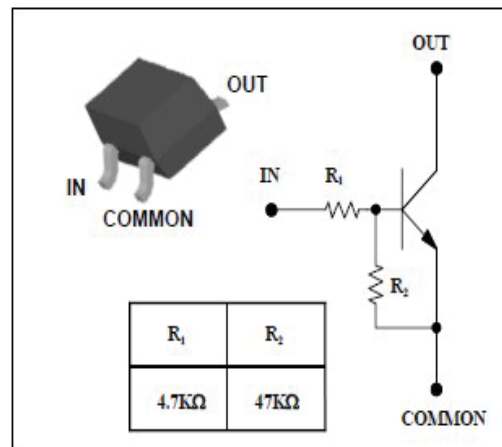
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density
- NPN Silicon Transistor

MECHANICAL DATA

- Case style:SOT-23 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Characteristic	Symbol	Ratings	Unit
Output voltage	V_O	50	V
Input voltage	V_I	20,-5	V
Output current	I_O	100	mA
Power dissipation	P_D	200	mW
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Output cut-off current	$I_{O(OFF)}$	$V_O=50V, V_I=0$	-	-	500	nA
DC current gain	G_I	$V_O=5V, I_O=10mA$	80	200	-	-
Output voltage	$V_{O(ON)}$	$I_O=10mA, I_I=0.5mA$	-	0.1	0.3	V
Input voltage (ON)	$V_{I(ON)}$	$V_O=0.2V, I_O=5mA$	-	0.9	1.3	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_O=5V, I_O=0.1mA$	0.5	0.65	-	V
Transition frequency	f_T^*	$V_O=10V, I_O=5mA, f=1MHz$	-	200	-	MHz
Input current	I_I	$V_I=5V, I_O=0$	-	-	1.8	mA
Input resistor (Input to base)	R_1	-	3.3	4.7	6.1	KΩ
Input resistor (Base to common)	R_2	-	33	47	61	KΩ

* : Characteristic of transistor only

RATINGS AND CHARACTERISTIC CURVES

Fig. 1 $P_D - T_a$

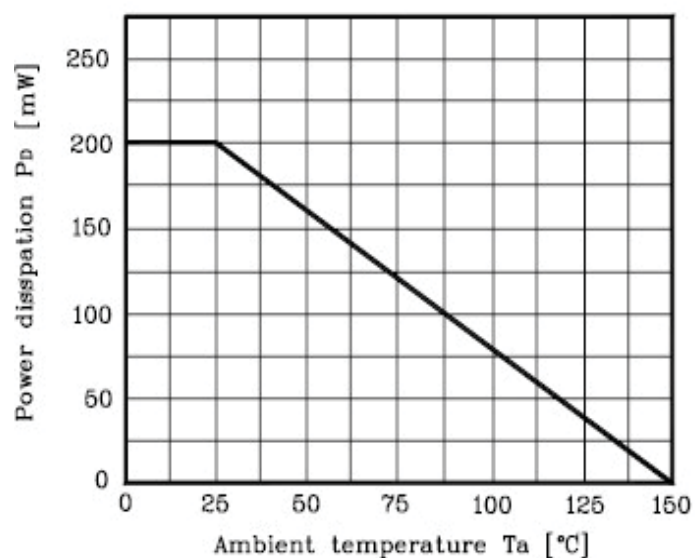


Fig. 2 $I_O - V_{I(ON)}$

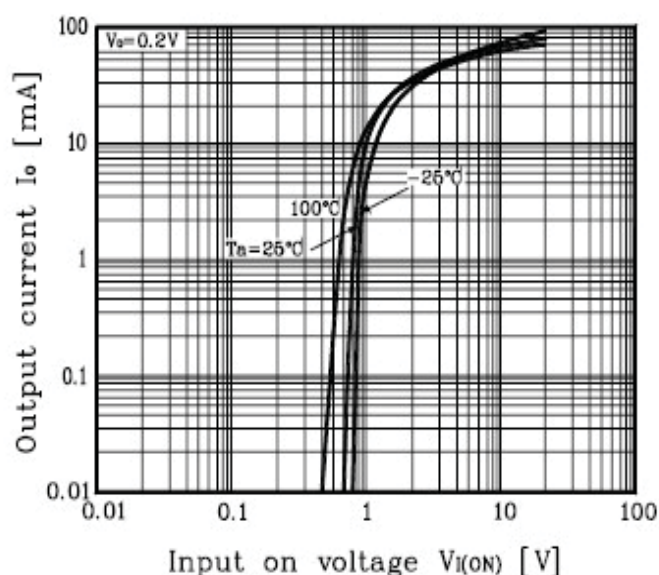


Fig. 3 $I_O - V_{I(OFF)}$

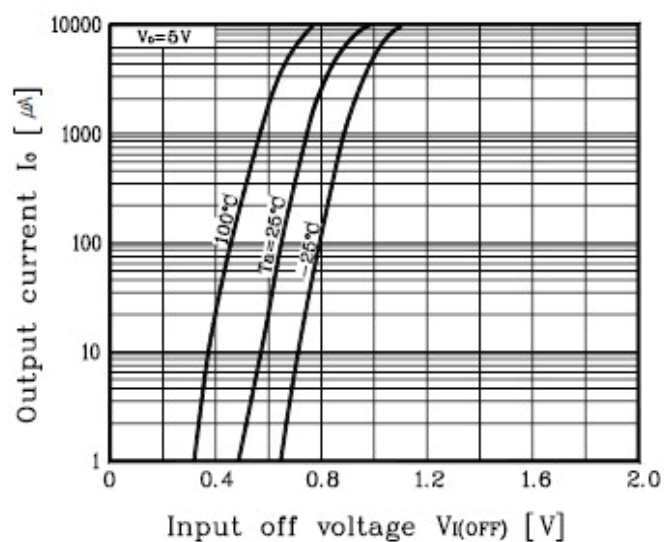
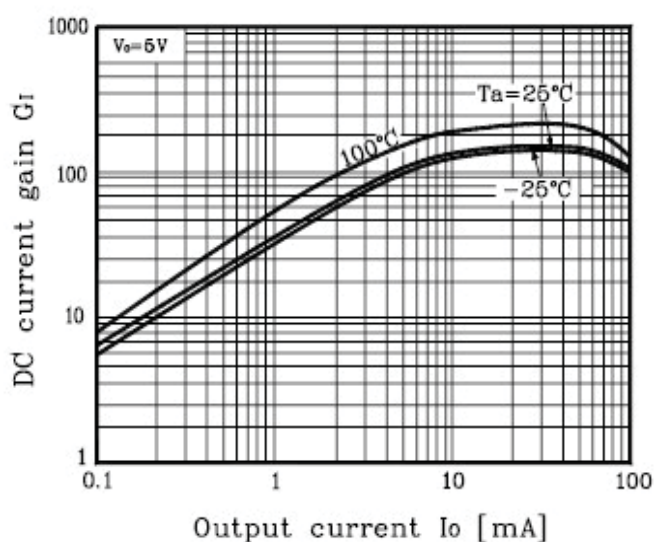
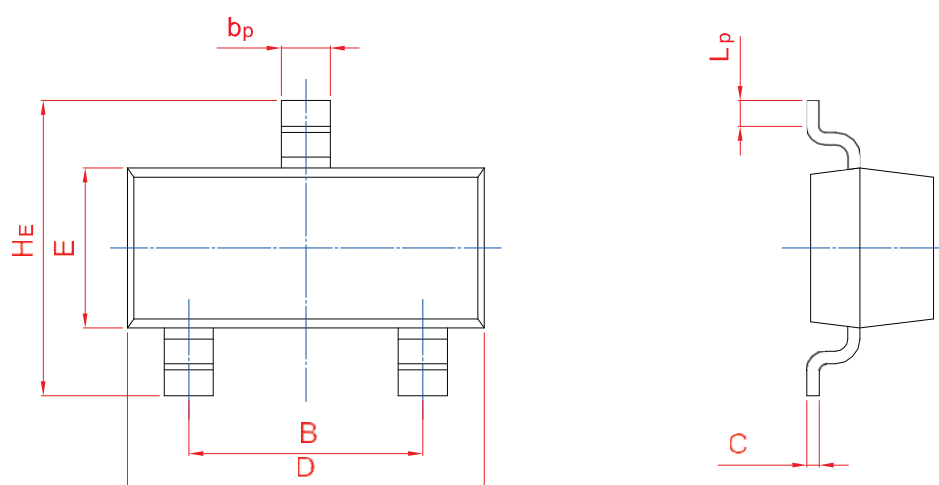


Fig. 4 $G_I - I_O$





UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20